

Criterion for light localization in random amplifying media

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Abstract

Dimensionless conductance for light propagating through a random medium with amplification tends to diverge with an increase of gain. This raises questions on the applicability of the localization criteria based on this quantity. To circumvent this problem, we study the properties of the ratio between the transmission (conductance) and the energy stored in the random medium. We argue that the generalized conductance $g_G = g \cdot (\mathcal{E}_0/\mathcal{E})$ – conductance normalized by the energy buildup (ratio between energy stored in the medium with gain \mathcal{E} to that in the passive system \mathcal{E}_0) – may be a convenient quantity on which a localization criterion can be built.

Key words: Wave propagation in random media, Anderson localization, Amplification, Random lasers

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1. Introduction

Anderson localization [1] (AL) of electrons can be understood as the effect due to repeated self-interference of de Broglie waves during their propagation in a random medium and the resulting cessation of diffusion[2, 3]. Particle conservation, enforced because the carriers have charge, lies in the foundation of the concept of AL.

Since it has been recognized that AL is a wave phenomenon[4, 5, 6], there has been a number of experimental studies of *light* localization [7, 8, 9, 10, 11, 12]. Understanding the effect of dissipation[5], ubiquitous in optical systems, turned out to be essential for proper physical description and interpretation of experimental results. It also prompted the search[10] for an alternative criterion of localization in absorbing media. Coherent amplification, which leads to an altogether new physical phenomenon of random lasing[13], demands further refinement of the concept of AL and its criteria in active random media.

For passive systems, dimensionless conductance, g , averaged over an ensemble of macroscopically equivalent, but microscopically different disorder realizations, is closely related to a number of criteria used to define the onset of localization [14, 15]. It has deep physical roots in the scaling theory of localization [15, 16], where g uniquely determines the scaling function describing mesoscopic transport through random medium.

Transmittance is [17, 18, 19] the electromagnetic counterpart of conductance. This analogy with mesoscopic electronic transport makes it tempting to adopt the localization criteria (LC) based on g in passive systems. However, the LC developed for passive systems may not be applicable for random

26 media with gain/absorption. Indeed, in dissipative systems, $g \ll 1$ may not
27 be indicative of the presence of localization [20, 10]. Likewise, $g \gg 1$ in an
28 amplifying random medium may not necessarily preclude localization effects
29 [21, 22].

30 In case of absorption, an alternative criterion, based on the magnitude
31 of *fluctuation* of transmission normalized by its average, was put forward
32 [10]. When gain is present, such an approach presents a fundamental prob-
33 lem. Indeed, there exists a non-zero probability of encountering a special
34 realization within the ensemble where the given value of the gain parameter
35 exceeds threshold for random lasing [23] (TRL). Without saturation effects,
36 such realizations make the statistics ill-defined. Inclusion of the saturation
37 introduces a dependence on system- and material-specific parameters which
38 are not associated with wave-transport properties of the random medium.
39 To avoid such dependence, and at the same time to regularize the statistical
40 ensemble, in Ref. [23] we introduced conditional statistics by excluding the
41 diverging contributions. We found that correlation linewidth $\delta\omega$ obtained in
42 such ensemble, can be used to define Thouless parameter $\delta = \delta\omega/\Delta\omega$ in ran-
43 dom medium with gain. Here $\Delta\omega$ is the average mode spacing which is equal
44 to the reciprocal of the density of states in the system. It was shown [23] that
45 $g = \delta$ relationship does not hold in non-passive systems. Nonetheless, the
46 decrease of δ with an increase of gain strength correlated with enhancement
47 of fluctuations of conductance normalized by its average [21]. These observa-
48 tions motivated us to explore analogies between the effects of amplification
49 and localization in random media.

50 Although the conditional statistics approach turned out to be fruitful, it

51 may be justified in weakly scattering media and when the gain parameter
 52 is far from the diffusive TRL. In strongly scattering media where sample-to-
 53 sample fluctuations are pronounced, a different approach is needed.

54 In this work, we investigate another way of regularizing statistics of trans-
 55 port through random media with amplification, with the goal of identify-
 56 ing a quantity on which the localization parameter can be based. When
 57 taken separately, both transmittance (conductance) and the energy inside
 58 the system $\mathcal{E} = \int_V W(\mathbf{r}, \omega) dV$ exhibit the divergent behavior as TRL is
 59 approached. Here, $W(\mathbf{r}, \omega) = n^2(\mathbf{r}, \omega) E^2(\mathbf{r}, \omega)$ is electromagnetic energy
 60 density expressed in terms of the refractive index and the local electric field.
 61 To counterbalance the divergent behavior of the transmittance, we propose
 62 to form a ratio, $g_G \propto T/\mathcal{E}$, between T and \mathcal{E} from the same disorder real-
 63 ization. In Section 2 we study the properties of the ratio T/\mathcal{E} in diffusive
 64 and localized regimes. In Section 3, based on T/\mathcal{E} , we introduce generalized
 65 conductance and discuss its properties.

66 **2. T/\mathcal{E} ratio in random medium**

67 *2.1. Diffusive regime in slab geometry*

68 Lets consider the effect of gain on T and \mathcal{E} in an optically thick ($\ell \ll L$)
 69 slab of 3D random medium described by the diffusive equation. The slab
 70 thickness is L , $D = c\ell/3$ is the diffusion coefficient, c – speed of light, ℓ –
 71 transport mean free path; $l_g = \tau_g c$ is (ballistic) gain length. The transmis-
 72 sion and reflection coefficients can be directly obtained from the solution for
 73 an absorbing slab in Ref. [24] through formal substitution $l_a = -l_g$. Such
 74 treatment of gain in a scattering problem has become known as the “neg-

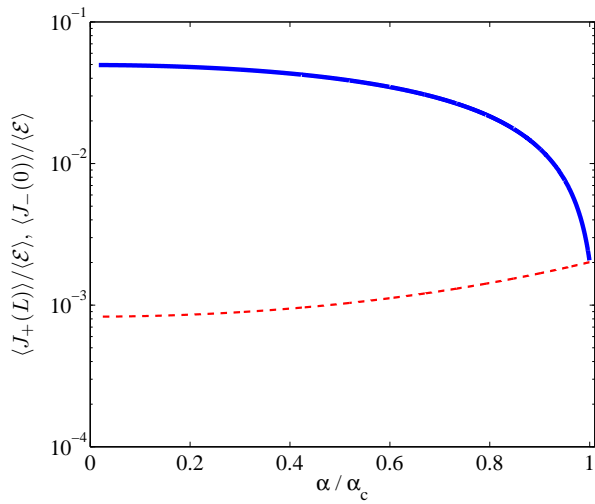


Figure 1: Transmission $\langle J_+(L) \rangle$ and reflection $\langle J_-(L) \rangle$ fluxes normalized by the value of total energy stored inside random medium (solid and dashed lines respectively) are plotted as functions of gain strength for a slab of random medium of thickness $L/\ell = 100$. The divergence in the vicinity of TRL is prevented due to the normalization – both curves approach the same limiting value.

75 ative absorption” model. It has been successfully used to describe turbid
 76 amplifying medium such as incoherent random lasers [25, 26, 27].

77 In Fig. 1 we plot the ratios of reflection (flux) to energy $\langle J_-(0) \rangle / \langle \mathcal{E} \rangle$ and
 78 transmission (flux) to energy $\langle J_+(L) \rangle / \langle \mathcal{E} \rangle$. For brevity we will refer to these
 79 quantities as $\langle R \rangle / \langle \mathcal{E} \rangle$ and $\langle T \rangle / \langle \mathcal{E} \rangle$. Within framework of the above model, we
 80 make the following observations: (a) Sufficiently close to TRL, the reflection
 81 and transmission fluxes diverge and become almost equal. This signifies the
 82 fact that the system approaches the regime when the gain alone can sustain
 83 its energy, without relying on the incident flux; (b) When normalized by
 84 the total energy in the slab, both $\langle R \rangle / \langle \mathcal{E} \rangle$ and $\langle T \rangle / \langle \mathcal{E} \rangle$ do not diverge when
 85 the TRL is approached. Instead, they converge to the finite value of $2\pi D\alpha_c$
 86 (where $\alpha^{-1} = \sqrt{\ell_g/3}$ and $\alpha_c \approx \pi/L$); (c) The change of the quantities
 87 $\langle R \rangle / \langle \mathcal{E} \rangle$ and $\langle T \rangle / \langle \mathcal{E} \rangle$ is related to modification of the intensity distribution
 88 inside the volume of random medium. When intensity $\langle I(z) \rangle$ assumes the
 89 limiting profile given by the lowest order diffusion mode, $\langle I(z) \rangle \simeq \sin(\pi z/L)$,
 90 the ratios $\langle R \rangle / \langle \mathcal{E} \rangle$ and $\langle T \rangle / \langle \mathcal{E} \rangle$ saturate.

91 As we are interested in the interplay between the effects of gain and light
 92 localization, we note that the diffusive description of this section has lim-
 93 itations: (i) the diffusion approximation fails when wave phenomena such
 94 as localization or coherent random lasing become important – proper treat-
 95 ment of electric field and its phase becomes necessary; (ii) an increase of gain
 96 or scattering are expected to lead to a buildup of fluctuations of transport
 97 coefficients [28, 23]. Thus, quantity, e.g., $\langle T \rangle / \langle \mathcal{E} \rangle$ will no longer adequately
 98 represent T/\mathcal{E} and instead should be replaced with $\langle T/\mathcal{E} \rangle$, which accounts for
 99 correlation between T and \mathcal{E} in the same sample; (iii) with further increase

100 of gain toward TRL, the divergence of fluctuations of T may necessitate the
101 consideration of higher moments of T/\mathcal{E} or, perhaps, its entire distribution;
102 (iv) at the onset of random lasing, nonlinear [29] and dynamical [30] pro-
103 cesses become essential for proper description of the system properties and
104 thus, CW quantity such as $\langle T/\mathcal{E} \rangle$ may no longer be suitable.

105 *2.2. Localized regime in one-dimension*

106 To investigate the effects (i-iii) from the previous section on T/\mathcal{E} , we
107 consider a system in localized regime . For this purpose a one-dimensional
108 (1D) model is already sufficient. Long enough 1D systems are necessarily in
109 the localized regime and, therefore, fluctuation effects will be essential even
110 at small values of gain.

111 We model the normal propagation of EM wave through a stack of dielec-
112 tric slabs (a 1D system) using 2×2 transfer matrices[31, 32, 33, 34]. The
113 randomness is introduced through the fluctuations of the refractive indexes
114 of the slabs whereas the imaginary part of the index gives rise to linear gain.
115 We use this numerical model to simulate the continuous-wave (CW) response
116 of the random system within certain spectral range.

117 Motivated by our analysis in section 2.1, we would like to study the
118 dependence of the ratio between transmission and stored energy in the above
119 wave-model. Our analysis shows that T and \mathcal{E} are not closely correlated
120 in the localized regime. We find substantially more resonant peaks in the
121 transmission coefficient with only about half of which have their counterparts
122 in the energy. This disparity is an additional source of fluctuation in the ratio
123 T/\mathcal{E} [34]. The goal of this section is to understand this behavior.

124 The field distribution inside the sample gives a clue why the energy may

125 differ from resonance to resonance. At the off-resonant frequencies we observe
126 nearly exponential decay. Whereas at or in the vicinity of a tunneling reso-
127 nance, two qualitatively distinct behaviors are observed. They are illustrated
128 in Fig. 2.

129 In the first scenario, c.f. bold line in Fig. 2, the electric field grows
130 exponentially (the characteristic length is equal to the localization length,
131 ξ) towards the localization center x_0 and falls off after it. Such behavior is
132 attributed[35] to the phenomenon of resonant tunneling via a localized state
133 centered at x_0 .

134 In the other case, c.f. thin line in Fig. 2, an additional negative expo-
135 nential segment can be identified. Because this type of behavior leads to
136 significantly lesser amount of energy stored inside the system, the resonances
137 of this type do not show a pronounced spectral peak in $\mathcal{E}(\omega)$. Although the
138 localized states with a single cusp in their spatial profiles were studied in Ref.
139 [35], the second scenario exemplified by thin line in 2 was not described in
140 the studies by Azbel and coworkers. We note that a multi-peaked spatial in-
141 tensity distribution is expected in case of so-called necklace states[36, 37, 38]
142 when two or more resonant states coexist at (almost) the same energy in the
143 given disorder realization. This behavior has lower probability of occurrence
144 in $\xi \ll L$ regime compared to the single states as in Fig. 2.

145 We find [34] that the difference in two types of behavior in Fig. 2 origi-
146 nates from the spatial location of the localized state: (i) at the frequencies
147 where peaks in transmission and energy occur simultaneously, the center of
148 localization is located in the first half of the sample $0 < x_0 < L/2$ (bold line
149 in Fig. 2); (ii) at the frequencies where peak in transmission has significantly

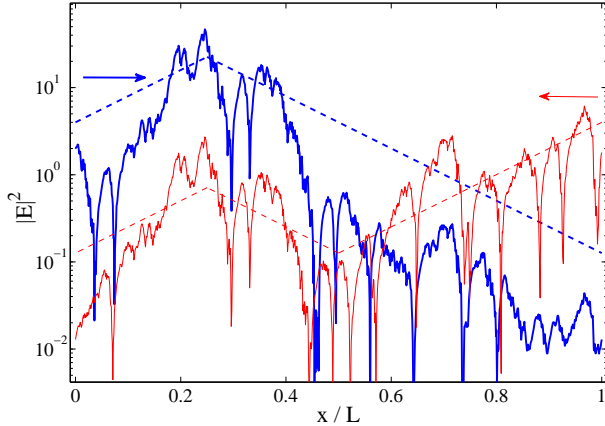


Figure 2: Two types of the on-resonance electric field distribution inside random medium with the center of localization in the first half (bold lines) and the second half (thin lines) of the sample. In the second case, the same mode is excited by shining the light onto the system from the right. Due to reciprocity, the value of transmission coefficient for both cases is exactly the same. However, the amount of energy stored inside the system is exponentially smaller in the second case. The latter resonance does not show noticeable peak in $\mathcal{E}(\omega)$. The dashed lines are the schematic envelope functions formed from segments with $\exp(\pm x/\xi)$ spatial dependences.

150 less pronounced (or non-distinguishable) peak in energy, the center of local-
 151 ization is located in the second half of the sample $L/2 < x_0 < L$ (thin line
 152 in Fig. 2); (iii) both profiles can be observed in the same sample at the same
 153 frequency by illuminating the system from left or right, see Fig. 2).

154 The non-monotonous behavior of the wavefunction can be understood
 155 intuitively as follows. In the regions away from a localization center the waves
 156 propagate via tunneling. There exist local solutions of Maxwell equation with
 157 an exponentially increasing and an exponentially decreasing envelopes [39].
 158 Balance between these two components is determined from the boundary
 159 conditions. It appears [34] that in $L/2 < x_0 < L$ case, the exponentially

160 increasing component has very small magnitude at the left boundary, but
161 becomes dominant at the turning point $x_T = 2x_0 - L$. In contrast, when the
162 localization center is located in the first half of the sample, the exponentially
163 increasing component is dominant right from the left boundary of the sample.

164 Our analysis above shows that T/\mathcal{E} parameter may not be unique in a
165 given sample – in general, it depends on the direction of illumination. This
166 observation seems to suggest that such ratio may be of a limited use as a
167 localization parameter. However, this limitation can be overcome via simple
168 normalization as we show in Section 3. Furthermore, in its present form,
169 T/\mathcal{E} possesses a unique property which we discuss next.

170 *2.3. Evolution of T/\mathcal{E} with the increase of gain*

171 As we observed in Section 2.1, a change in T/\mathcal{E} with gain is indicative of a
172 modification of the intensity profile inside a diffusive slab. Similar conclusions
173 can be made in the localized regime. Here we employ the model described
174 in Section 2.2.

175 Our simulations demonstrate that a change in T/\mathcal{E} indeed signifies the
176 modification of the field distribution inside the random medium. Interest-
177 ingly, we find that such modifications can be very dramatic in the localization
178 regime. Fig. 3 illustrates this effect. At first glance, this seems to disagree
179 with the conclusions in Refs. [40, 41, 42] where (in localized regime) little or
180 no change in the field pattern was found with an increase of amplification.
181 The apparent discrepancy can be explained if one compares the methods
182 used to excite the system. In our work, we consider the transmission experi-
183 ment setup, whereas in the previous works [40, 41, 42] the system was excited
184 throughout its entire volume or relatively close to the center of localization.

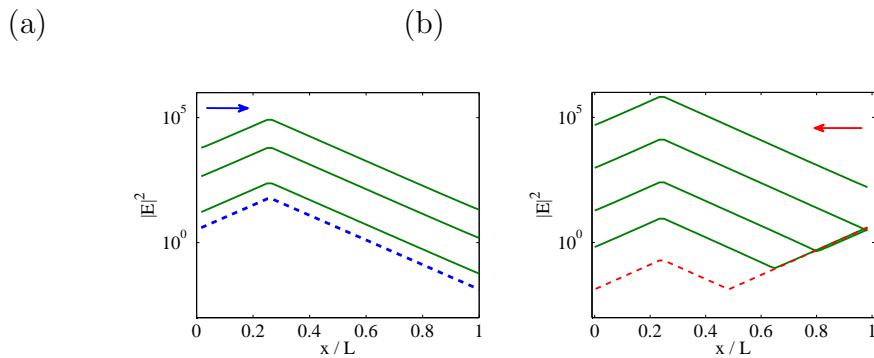


Figure 3: An illustration of the effect gain on the electric field distribution in 1D random medium. A periodic stack of alternating dielectric layers with a defect at $x_0 = L/4$ is considered. As demonstrated in Ref. [34], such model qualitatively describes the field profiles (such as those in Fig. 2) in the random media. Panels (a) and (b) show the field envelopes obtained when the system is illuminated (at resonant frequency) from the left and right respectively. Dashed lines correspond to the passive medium. The solid curves (from bottom up) are obtained for $l_{g,cr}/l_g$ equal to 0.5, 0.9, 0.99 in (a) and 0.85, 0.95, 0.98, 0.99 in (b). The field distribution in (b) shows a dramatic modification with an increase of gain.

185 Under such excitation conditions, the situation shown in Fig. 3a is always re-
 186 alized [34]. We also note that the mode distribution in Fig. 3b was observed
 187 to converge to that in Fig. 3a when the gain approached its critical value.
 188 when the field distribution is maintained by the gain with little reliance on
 189 the incident energy.

190 **3. Discussion**

191 Although the ratio T/\mathcal{E} did not have the tendency to diverge when gain
 192 approached its TRL value, it exhibited additional fluctuation due to orienta-
 193 tion of the system, Sections 2.2,2.3. It should be noted that due to reciprocity,
 194 transmission T (or more generally conductance) is independent of direction
 195 of illumination – it is the same for both field distributions depicted in Fig. 2.

196 To circumvent the above problem while retaining the desired non-singular
 197 behavior in the vicinity of TRL, we introduce the following parameter

$$g_G = T/\mathcal{E} \times \mathcal{E}_0. \quad (1)$$

198 Here \mathcal{E}_0 is the energy stored in the random medium with no gain. All the
 199 quantities entering Eq. (1) should be evaluated for each disorder realization
 200 prior to any statistical analysis. By construction, g_G reduces to the trans-
 201 mission in a 1D system without gain and becomes conventional (average)
 202 conductance upon statistical averaging in higher dimensional systems. Thus
 203 we will refer to g_G as generalized conductance.

204 By definition, the quantity \mathcal{E}_0 is equal to volume-integrated electromag-
 205 netic energy density in passive system. The latter coincides [43] with density
 206 of electromagnetic states, which is an important energy scale that enters

207 such localization criteria as Thouless number δ . Therefore, the generalized
208 conductance can be interpreted as the conductance in the random medium
209 with gain scaled down by the energy buildup factor $\mathcal{E}/\mathcal{E}_0$. This normalization
210 offsets the tendency of the conductance to diverge in a random medium with
211 gain and avoids introducing artifacts such as the orientation dependence.

212 In future, we plan to investigate both theoretically and experimentally the
213 statistical properties of the generalized conductance in Eq. (1) in random
214 medium with gain. Experimentally, all components of g_G can be determined
215 from near-field scanning measurements in two-dimensional random media –
216 structurally disordered semiconductor films. This opens up a possibility to
217 corroborate and extend the results of this study.

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